

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

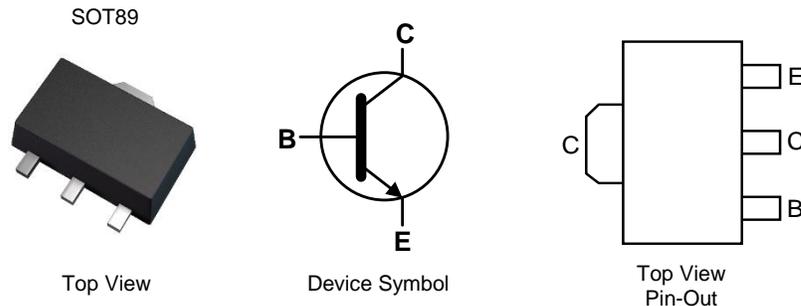
- $BV_{CEO} > 80V$
- $I_C = 1A$ High Continuous Collector Current
- $I_{CM} = 2.0A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < 500mV @ 0.5A$
- Epitaxial Planar Die Construction
- Complementary PNP types: BCX5316Q
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Leads,
Solderable per MIL-STD-202 Method 208 Ⓔ3
- Weight: 0.055 grams (Approximate)

Applications

- Automotive
- Medium Power Switching or Amplification Applications
- AF Driver and Output Stages

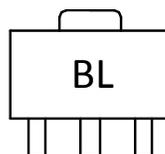


Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCX5616QTA	Automotive	BL	7	12	1,000
BCX5616QTC	Automotive	BL	13	12	4,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



BL = Product Type Marking Code

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	1	A
Peak Pulse Collector Current	I_{CM}	2.0	
Continuous Base Current	I_B	100	mA
Peak Pulse Base Current	I_{BM}	200	

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

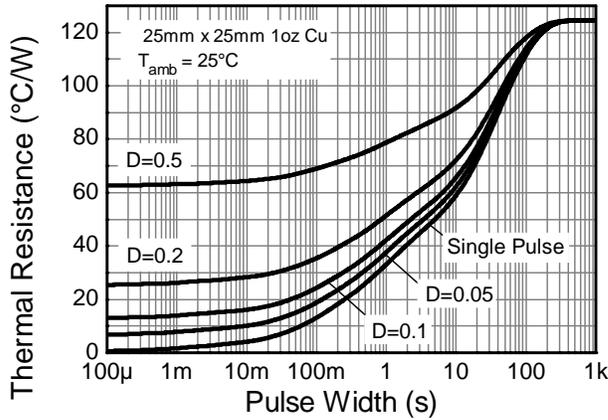
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	(Note 6)	1
		(Note 7)	1.5
		(Note 8)	2.0
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	(Note 6)	125
		(Note 7)	83
		(Note 8)	60
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	13	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^\circ\text{C}$

ESD Ratings (Note 10)

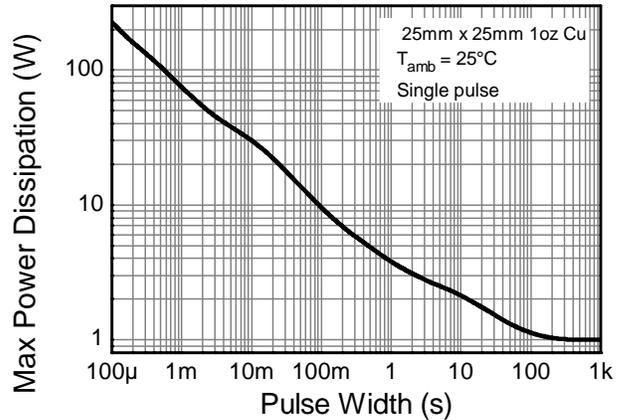
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as note (6), except the device is mounted on 25mm x 25mm 1oz copper.
 8. Same as note (6), except the device is mounted on 50mm x 50mm 1oz copper.
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

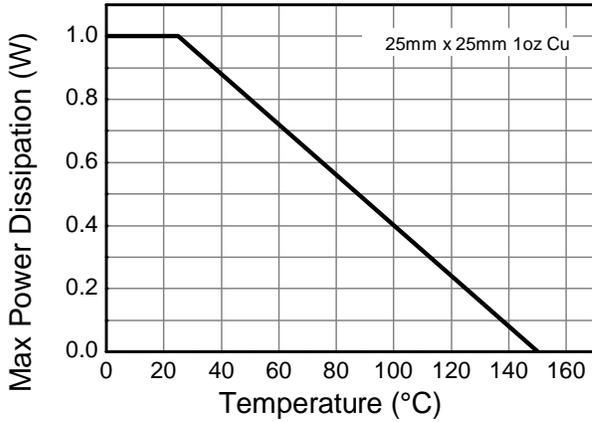
Thermal Characteristics and Derating Information



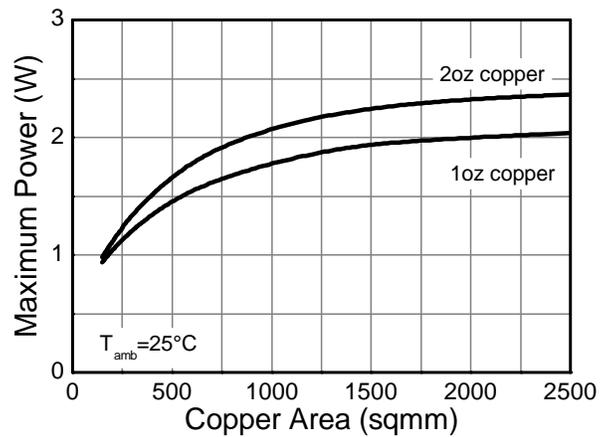
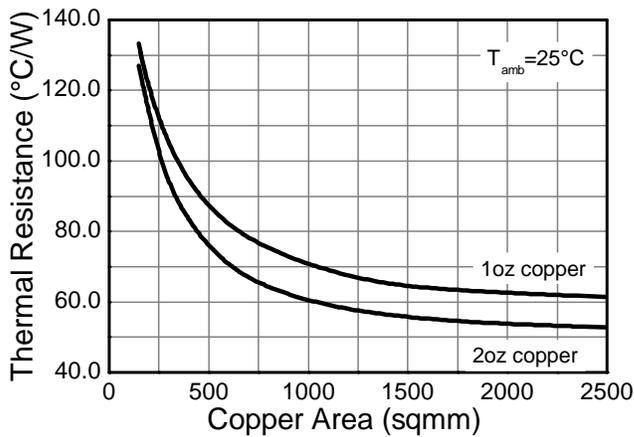
Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve



Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	100	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	80	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	6	—	—	V	$I_E = 100\mu\text{A}$
Collector Cut-off Current	I_{CBO}	—	—	0.1 20	μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}, T_A = +150^\circ\text{C}$
Emitter Cut-off Current	I_{EBO}	—	—	20	nA	$V_{EB} = 5\text{V}$
Static Forward Current Transfer Ratio (Note 11)	h_{FE}	25 100 25	— — —	- 250 -	—	$I_C = 5\text{mA}, V_{CE} = 2\text{V}$ $I_C = 150\text{mA}, V_{CE} = 2\text{V}$ $I_C = 500\text{mA}, V_{CE} = 2\text{V}$
Collector-Emitter Saturation Voltage (Note 11)	$V_{CE(sat)}$	—	—	0.5	V	$I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	—	—	1.0	V	$I_C = 500\text{mA}, V_{CE} = 2\text{V}$
Transition Frequency	f_T	150	—	-	MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	25	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

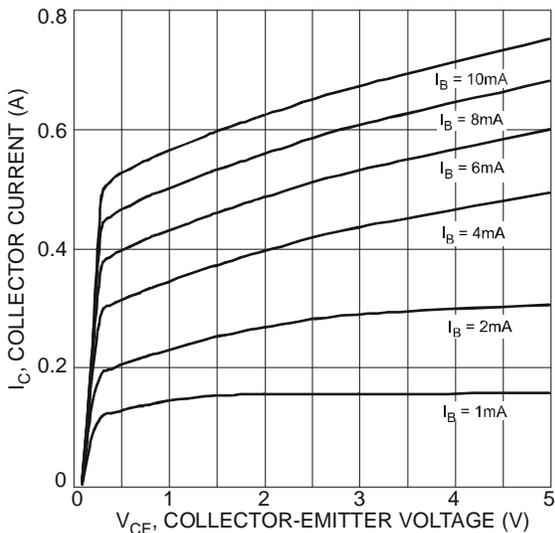
 Note: 11. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.


Fig. 1 Typical Collector Current vs. Collector-Emitter Voltage

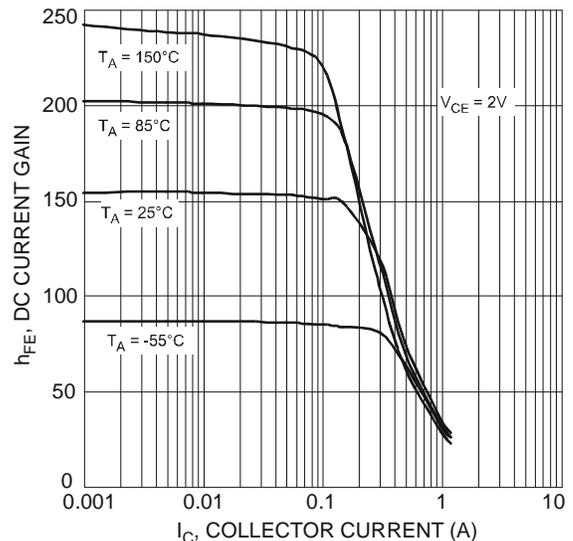


Fig. 2 Typical DC Current Gain vs. Collector Current

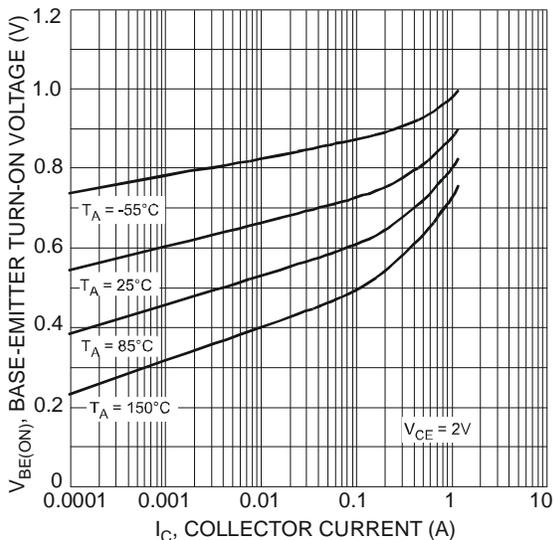


Fig. 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

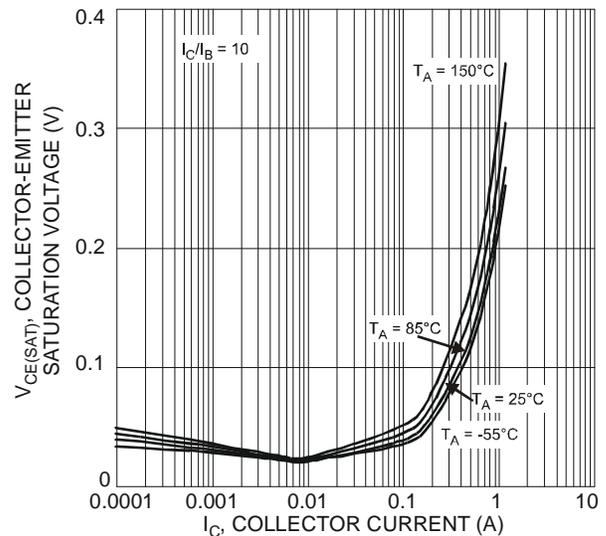


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

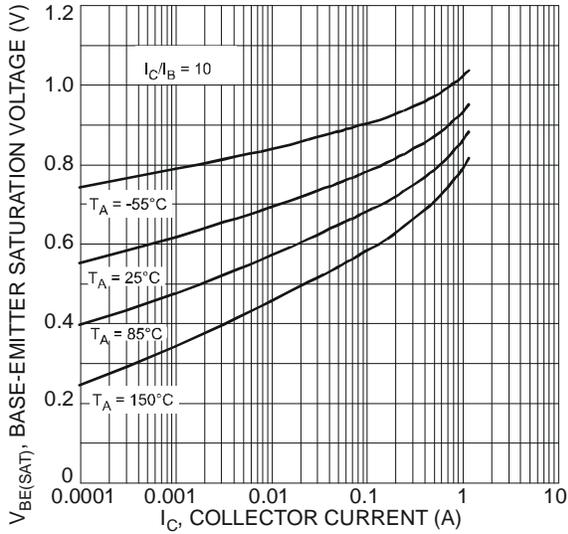


Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

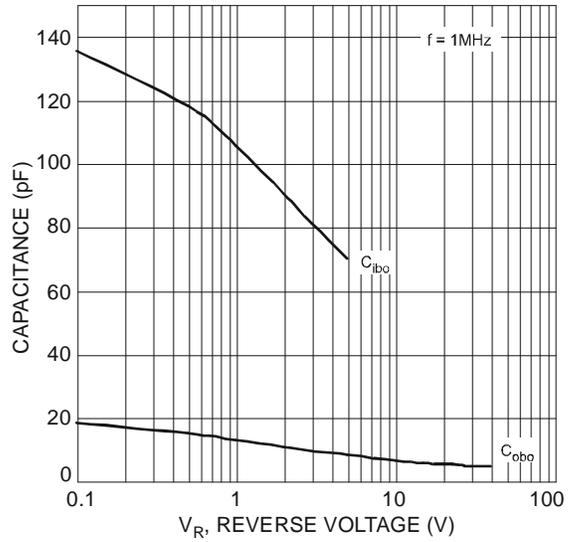


Fig. 6 Typical Capacitance Characteristics

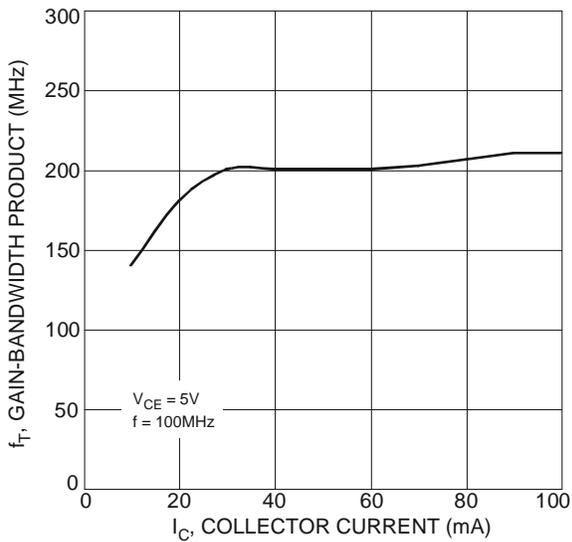
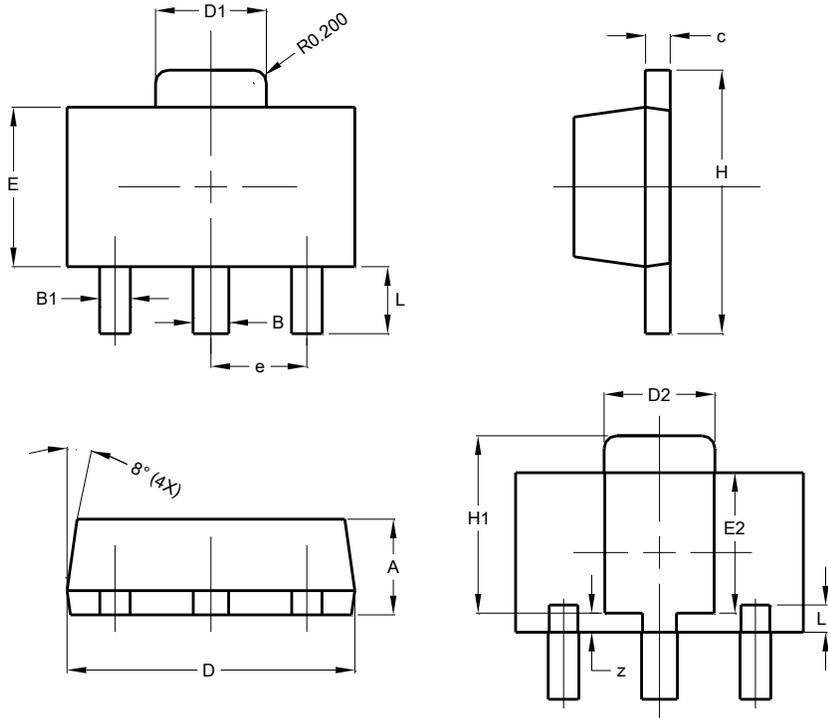


Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

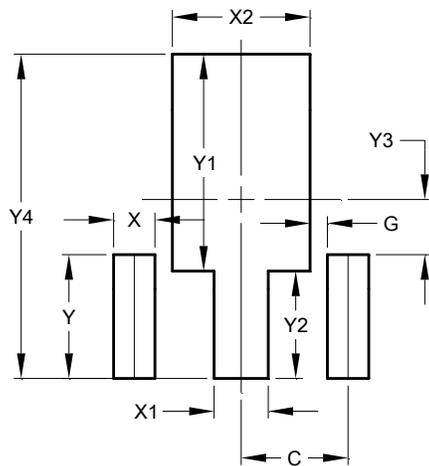
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.427 REF		
Z	0.30 REF		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

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